

# Matthew J Smith

## List of Publications by Year in descending order

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12  
papers

400  
citations

840776

11  
h-index

1199594

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g-index

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12  
docs citations

12  
times ranked

421  
citing authors

#	ARTICLE	IF	CITATIONS
1	Femtosecond-laser hyperdoping silicon in an SF <sub>6</sub> atmosphere: Dopant incorporation mechanism. Journal of Applied Physics, 2015, 117, 125301.	2.5	24
2	Origin of the visible emission of black silicon microstructures. Applied Physics Letters, 2015, 107, .	3.3	7
3	Improving dopant incorporation during femtosecond-laser doping of Si with a Se thin-film dopant precursor. Applied Physics A: Materials Science and Processing, 2014, 114, 1009-1016.	2.3	27
4	Morphological stability during solidification of silicon incorporating metallic impurities. Journal of Applied Physics, 2014, 115, 163516.	2.5	15
5	Supersaturating silicon with transition metals by ion implantation and pulsed laser melting. Journal of Applied Physics, 2013, 114, .	2.5	59
6	Depth-resolved cathodoluminescence spectroscopy of silicon supersaturated with sulfur. Applied Physics Letters, 2013, 102, .	3.3	14
7	Correlating stress generation and sheet resistance in InAlN/GaN nanoribbon high electron mobility transistors. Applied Physics Letters, 2012, 101, 113101.	3.3	11
8	The origins of pressure-induced phase transformations during the surface texturing of silicon using femtosecond laser irradiation. Journal of Applied Physics, 2012, 112, .	2.5	59
9	Studying femtosecond-laser hyperdoping by controlling surface morphology. Journal of Applied Physics, 2012, 111, 093511.	2.5	35
10	High-Electron-Mobility Transistors Based on InAlN/GaN Nanoribbons. IEEE Electron Device Letters, 2011, 32, 1680-1682.	3.9	34
11	Pressure-induced phase transformations during femtosecond-laser doping of silicon. Journal of Applied Physics, 2011, 110, .	2.5	79
12	The effects of a thin film dopant precursor on the structure and properties of femtosecond-laser irradiated silicon. Applied Physics A: Materials Science and Processing, 2011, 105, 795-800.	2.3	36